

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	10	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or JP-2004153112-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or JP-2002329860-\$ or JP-01128575-\$ or KR-010082828-\$ or KR-100332124-\$ or JP-2001125135-\$	DERWENT	OR	OFF	2005/03/31 07:45
S2	3	(buffer near conductive) adj film	DERWENT	OR	ON	2005/03/30 18:36
S3	16	(buffer near conductive) adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/30 18:38
S4	3	"798574".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/30 18:42
S5	463	(thin adj film adj transistor or tft) and amorphous adj silicon WITH buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/31 16:55
S6	94	hoon near kim	US-PGPUB; USPAT	OR	OFF	2005/03/30 19:10
S7	3	(thin adj film adj transistor or tft) and S6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/30 19:11
S8	454	(etch etching etchant etched pattern patterned patterning) near4 buffer and (thin adj film adj transistor or tft)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/03/30 19:16
S10	19	((("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904")) PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/31 07:44

S11	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	DERWENT	OR	ON	2005/03/31 07:47
S12	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 07:48
S14	28	S10 or S12	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 07:49
S15	8	(S10 or S12) and (hoon near kim or thin adj film adj transistor or tft)	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 07:50
S16	25	(S10 or S12) and (etch etching etchant etched pattern patterned patterning)	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 09:30
S17	17	S16 not S15	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 07:51
S18	3	S14 not (S16 or S15)	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 08:00
S19	3	S18 and buffer	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 08:01
S20	1	(US-20040207015-\$).did.	US-PGPUB	OR	OFF	2005/03/31 09:30
S21	1	S20 and buffer and activation and gate adj insulation and (etch etching etchant etched pattern patterned patterning)	US-PGPUB; USPAT; JPO	OR	ON	2005/03/31 09:30
S23	208	(thin adj film adj transistor or tft) and amorphous adj silicon WITH buffer	USPAT	OR	ON	2005/03/31 12:50
S24	7228	"117"/\$3.ccls.	USPAT	OR	ON	2005/03/31 09:36
S25	15	S23 and S24	USPAT	OR	ON	2005/03/31 09:36
S26	3043	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:27

S28	2569	S26 and step not step adj for	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:20
S29	985	S26 and "257"/\$3.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:21
S30	25852	gate adj (insulator insulating insulation insulated insulate oxide) WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:27
S31	382	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:28
S32	14778	S30 and (nm nanometer angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:28
S33	285	S31 and (nm nanometer angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 10:28
S34	168	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:49
S35	6320	(Park-Kee\$ or Yoo-J\$ or Han-M\$). in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/31 12:50
S36	18	(thin adj film adj transistor or tft) and amorphous adj silicon and S35	USPAT	OR	ON	2005/03/31 14:03

S42	112	(thin adj film adj transistor or tft) and amorphous adj silicon and over and etch and (over-etch "over etch")	US-PGPUB; USPAT	OR	ON	2005/03/31 14:08
S44	14598	S14 S32 S34 S36 S42	US-PGPUB; USPAT; JPO	OR	OFF	2005/03/31 15:12
S46	25	"4,767,723"	US-PGPUB; USPAT	OR	ON	2005/03/31 15:11
S48	14509	S14 S32 S34 S36	US-PGPUB; USPAT; JPO	OR	OFF	2005/03/31 15:12
S51	235	S14 S34 S36 S46	US-PGPUB; USPAT; JPO	OR	OFF	2005/03/31 15:13
S52	110	S42 not S51	US-PGPUB; USPAT	OR	OFF	2005/03/31 15:14
S54	7268	(257/347,350,390,40,51,57,59,66, 72).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/04 13:33
S55	3186	S54 and (tft thin adj film adj transistor)	US-PGPUB; USPAT	OR	OFF	2005/04/01 09:36
S56	789	S55 and buffer	US-PGPUB; USPAT	OR	OFF	2005/04/01 09:36
S57	19	((("6777747") or ("6534788") or ("6528855") or ("6509234") or ("6396079") or ("6033941") or ("5510640") or ("5196717") or ("5173753") or ("5144401") or ("4715930") or ("4287661") or ("4035198") or ("20040173812") or ("20040084722") or ("20040005740") or ("20030122178") or ("20020054247") or ("6746904"))). PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/01 09:37
S58	9	JP-63093150-\$ or JP-61078138-\$ or JP-02031464-\$ or US-6809349-\$ or JP-04096337-\$ or JP-04101432-\$ or JP-02281634-\$ or US-6638825-\$ or JP-01128575-\$	US-PGPUB; USPAT; JPO	OR	ON	2005/04/01 09:37
S59	28	S57 or S58	US-PGPUB; USPAT; JPO	OR	ON	2005/04/01 09:37

S60	25852	gate adj (insulator insulating insulation insulated insulate oxide) WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 09:37
S61	382	(thin adj film adj transistor or tft) and amorphous adj silicon and buffer WITH thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 09:37
S62	14778	S60 and (nm nanometer angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 09:37
S63	285	S61 and (nm nanometer angstrom)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 09:37
S64	168	S62 and S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 09:37
S65	6320	(Park-Kee\$ or Yoo-J\$ or Han-M\$). in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/01 09:37
S66	18	(thin adj film adj transistor or tft) and amorphous adj silicon and S65	USPAT	OR	ON	2005/04/01 09:37
S67	112	(thin adj film adj transistor or tft) and amorphous adj silicon and over and etch and (over-etch "over etch")	US-PGPUB; USPAT	OR	ON	2005/04/01 09:37
S68	25	"4,767,723"	US-PGPUB; USPAT	OR	ON	2005/04/01 09:37
S69	235	S59 S64 S66 S68	US-PGPUB; USPAT; JPO	OR	OFF	2005/04/01 09:37
S70	110	S67 not S69	US-PGPUB; USPAT	OR	OFF	2005/04/01 09:37

S71	783	S56 not S70	US-PGPUB; USPAT	OR	OFF	2005/04/01 09:41
S72	37	"4851363" not S54	US-PGPUB; USPAT	OR	OFF	2005/04/01 09:42
S73	5	"4851363" not S54 and buffer	US-PGPUB; USPAT	OR	OFF	2005/04/01 09:42
S76	356	("6268631" or "5929487" or "5112764" or "5130264" or "6124155" or "5264720" or "5492843" or "5523240" or "5534445" or "5595923" or "5605846" or "5830787" or "5837619" or "5946561" or "6004831" or "6008078" or "6008076" or "6150203" or "6335213" or "6706572" or "6709907") not ("6268631" or "5929487" or "56743" or "5112764" or "5130264" or "6124155" or "5264720" or "5492843" or "5523240" or "5534445" or "5595923" or "5605846" or "5830787" or "5837619" or "5946561" or "6004831" or "6008078" or "6008076" or "6150203" or "6335213" or "6706572" or "6709907").pn.	US-PGPUB; USPAT	OR	OFF	2005/04/01 10:42
S77	344	S76 not S70	US-PGPUB; USPAT	OR	OFF	2005/04/01 18:02
S78	1	("5,492,843").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/01 18:06
S79	1	S78 and base film and protection film	US-PGPUB; USPAT	ADJ	OFF	2005/04/01 18:14
S80	4	"5,492,843" and base film and protection film	US-PGPUB; USPAT	ADJ	OFF	2005/04/01 18:14
S81	20	(US-4949141-\$ or US-5112764-\$ or US-5130264-\$ or US-5264720-\$ or US-5492843-\$ or US-5523240-\$ or US-5534445-\$ or US-5595923-\$ or US-5605846-\$ or US-5830787-\$ or US-5837619-\$ or US-5946561-\$ or US-6004831-\$ or US-6008076-\$ or US-6008078-\$ or US-6124155-\$ or US-6150203-\$ or US-6335213-\$ or US-6706572-\$ or US-6709907-\$).did.	USPAT	OR	OFF	2005/04/04 10:49
S82	0	S81 and (sps ela)	USPAT	OR	OFF	2005/04/04 10:49
S83	1	S81 and (spc ela)	USPAT	OR	OFF	2005/04/04 10:51
S84	1	(US-20040109098-\$).did.	US-PGPUB	OR	OFF	2005/04/04 10:52

S85	0	S84 and (spc ela)	USPAT	OR	OFF	2005/04/04 11:35
S86	1	"798574".ap.	US-PGPUB	OR	OFF	2005/04/04 10:52
S87	1	S86 and (spc ela)	US-PGPUB	OR	OFF	2005/04/04 12:22
S88	1	("5569936").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/04 12:22
S89	12347	etch adj rate	US-PGPUB; USPAT	OR	OFF	2005/04/04 12:23
S90	15277	etch adj rate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 12:23
S91	2729	etch adj rate near4 (sin silicon si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:04
S92	76	S91 and process near4 etching near4 silicon adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:24
S93	15	"5,310,457"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/04 13:24
S94	1	("4949141").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/04 13:33